Gilles Dambrine

List of Publications by Year
in descending order

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167 papers	3,894 citations	236612 25 h-index	155451 55 g-index
167 all docs	167 docs citations	167 times ranked	2194 citing authors

#	Article	IF	Citations
1	Near-Field Scanning Millimeter-Wave Microscope Operating Inside a Scanning Electron Microscope: Towards Quantitative Electrical Nanocharacterization. Applied Sciences (Switzerland), 2021, 11, 2788.	1.3	2
2	Impact of GSG Probe to Pads Contact Repeatability for On-Wafer RF Measurements. , 2021, , .		5
3	High-Frequency Noise Characterization and Modeling of Graphene Field-Effect Transistors. IEEE Transactions on Microwave Theory and Techniques, 2020, 68, 2116-2123.	2.9	5
4	Control and Automation for Miniaturized Microwave GSG Nanoprobing. , 2020, , 751-768.		0
5	Fully Integrated Interferometry-Based Reflectometer for High-Impedance Instrumentation. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 3901-3908.	2.9	2
6	Small-signal characterization and modelling of 55nm SiGe BiCMOS HBT up to 325GHz. Solid-State Electronics, 2017, 129, 150-156.	0.8	16
7	Sensitivity and accuracy analysis in scanning microwave microscopy. , 2016, , .		12
8	The large world of FET small-signal equivalent circuits (invited paper). International Journal of RF and Microwave Computer-Aided Engineering, 2016, 26, 749-762.	0.8	43
9	Optimization of a microelectromechanical systems (MEMS) approach for miniaturized microcantilever-based RF microwave probes. Sensors and Actuators A: Physical, 2016, 238, 51-59.	2.0	12
10	RF wafer probing with improved contact repeatability using nanometer positioning. , 2016, , .		13
11	On-wafer probe station for microwave metrology at the nanoscale. , 2015, , .		2
12	MEMS-based RF probes for on-wafer microwave characterization of micro/nanoelectronics. , 2015, , .		2
13	Sub-fF 130 nm MOS Varactor Characterization Using 6.8 GHz Interferometry-Based Reflectometer. IEEE Microwave and Wireless Components Letters, 2015, 25, 418-420.	2.0	2
14	Nanorobotic RF probe station for calibrated on-wafer measurements. , 2015, , .		5
15	Integrated MEMS RF Probe for SEM Stationâ€"Pad Size and Parasitic Capacitance Reduction. IEEE Microwave and Wireless Components Letters, 2015, 25, 693-695.	2.0	8
16	Robotic on-wafer probe station for microwave characterization in a scanning electron microscope. , 2015, , .		3
17	Measurement accuracy and repeatability in near-field scanning microwave microscopy. , 2015, , .		10
18	Sub-10 nm-scale capacitors and tunnel junctions measurements by SMM coupled to RF interferometry. , 2015, , .		1

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19	MEMS probes for on-wafer RF microwave characterization of future microelectronics: design, fabrication and characterization. Journal of Micromechanics and Microengineering, 2015, 25, 075024.	1.5	14
20	Millimeter-Wave Characterization of Silicon Devices under Small-Signal Regime. , 2014, , 47-96.		0
21	Quantitative impedance characterization of sub-10 nm scale capacitors and tunnel junctions with an interferometric scanning microwave microscope. Nanotechnology, 2014, 25, 405703.	1.3	22
22	Miniaturized MEMS-based GSG probes for microwave characterization. , 2014, , .		6
23	Uncertainties assessment of noise parameters in D- band using in situ tuner techniques. , 2014, , .		1
24	1–20 Ghz kΩ-range BiCMOS 55 nm reflectometer. , 2014, , .		0
25	Measurement Techniques for RF Nanoelectronic Devices: New Equipment to Overcome the Problems of Impedance and Scale Mismatch. IEEE Microwave Magazine, 2014, 15, 30-39.	0.7	49
26	Nonlinear measurement of non periodic pulse train with mixer based NVNA dedicated to radar power amplifier. , 2014, , .		2
27	Nonlinear measurement dedicated to non periodic pulse train for radar power amplifier characterization. , 2014, , .		2
28	Graphene nanotransistors for RF charge detection. Journal Physics D: Applied Physics, 2014, 47, 094004.	1.3	6
29	RF and broadband noise investigation in <scp>Highâ€k/Metal Gate</scp> 28â€nm CMOS bulk transistor. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 736-747.	1.2	16
30	Millimeter-Wave In Situ Tuner: An Efficient Solution to Extract the Noise Parameters of SiGe HBTs in the Whole 130â€“170 GHz Range. IEEE Microwave and Wireless Components Letters, 2014, 24, 649-651.	2.0	8
31	Interferometric Near-field Microwave Microscopy Platform for Electromagnetic Micro-analysis. Procedia Engineering, 2014, 87, 388-391.	1.2	3
32	Miniaturized Microcantilever-based RF Microwave Probes Using MEMS Technologies. Procedia Engineering, 2014, 87, 692-695.	1.2	6
33	Measurement of the influence of non periodic pulse train on the nonlinear behavior of radar power amplifier using mixer based NVNA. , 2014, , .		0
34	High frequency noise characterisation of graphene FET device. , 2013, , .		10
35	RF noise investigation in High-k/Metal Gate 28-nm CMOS transistors. , 2012, , .		4
36	In Situ Silicon-Integrated Tuner for Automated On-Wafer MMW Noise Parameters Extraction Using Multi-Impedance Method for Transistor Characterization. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 170-177.	1.4	5

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37	Flexible Gigahertz Transistors Derived from Solution-Based Single-Layer Graphene. Nano Letters, 2012, 12, 1184-1188.	4.5	133
38	Millimeter wave field effect transistors produced using high purity semiconducting single-walled carbon nanotubes. , 2011, , .		0
39	InAs/AlSb HEMTs for cryogenic LNAs at ultra-low power dissipation. Solid-State Electronics, 2011, 64, 47-53.	0.8	15
40	Fabrication and Characterization of an Epitaxial Graphene Nanoribbon-Based Field-Effect Transistor. IEEE Transactions on Electron Devices, 2011, 58, 1594-1596.	1.6	24
41	Small signal and HF noise performance of 45 nm CMOS technology in mmW range. , 2011, , .		16
42	RF characterization of epitaxial graphene nano ribbon field effect transistor. , 2011, , .		3
43	Sb-HEMT: Toward 100-mV Cryogenic Electronics. IEEE Transactions on Electron Devices, 2010, 57, 1903-1909.	1.6	18
44	60ÂGHz current gain cut-off frequency graphene nanoribbon FET. International Journal of Microwave and Wireless Technologies, 2010, 2, 441-444.	1.5	3
45	Anisotropic transport properties in InAs/AlSb heterostructures. Applied Physics Letters, 2010, 97, .	1.5	20
46	Influence of temperature on high frequency performance of graphene nano ribbon field effect transistor. , 2010, , .		6
47	Gigahertz characterization of a single carbon nanotube. Applied Physics Letters, 2010, 96, 042109.	1.5	43
48	Validation of the 2 Temperatures Noise Model Using Pre-Matched Transistors in W-Band for Sub-65 nm Technology. IEEE Microwave and Wireless Components Letters, 2010, 20, 274-276.	2.0	4
49	Fabrication and characterization of 200-nm self-aligned In<inf>0.53</inf>Ga<inf>0.47</inf>As MOSFET. , 2010, , .		1
50	Narrow band gap IIIâ€“V based-FET for ultra low power high frequency analog applications. , 2009, , .		0
51	MMW lab In-Situ to extract noise parameters of 65nm CMOS aiming 70∼90GHz applications. , 2009, , .		4
52	In-Situ Silicon Integrated Tuner for Automated On-Wafer MMW Noise Parameters Extraction using Multi-Impedance Method for Transistor Characterization. , 2009, , .		7
53	Investigation of SiGe HBT potentialities under cryogenic temperature. , 2009, , .		6
54	Analog/RF Performance of Multichannel SOI MOSFET. IEEE Transactions on Electron Devices, 2009, 56, 1473-1482.	1.6	44

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55	Gate-Recess Technology for InAs/AlSb HEMTs. IEEE Transactions on Electron Devices, 2009, 56, 1904-1911.	1.6	24
56	A selective epitaxy collector module for high-speed Si/SiGe:C HBTs. Solid-State Electronics, 2009, 53, 873-876.	0.8	5
57	High frequency performance of sub-100nm UTB-FDSOI featuring TiN/HfO2 gate stack. Solid-State Electronics, 2009, 53, 433-437.	0.8	2
58	SiGe HBT noise parameters extraction using in-situ silicon integrated tuner in MMW range 60–110GHz. , 2009, , .		3
59	Overview of Carbon Nanotubes for High Frequency Electronics. , 2009, , .		0
60	DC characteristics of InAs/AlSb HEMTs at cryogenic temperatures. , 2009, , .		6
61	80 GHz field-effect transistors produced using high purity semiconducting single-walled carbon nanotubes. Applied Physics Letters, 2009, 94, .	1.5	153
62	Optimization of RF Performance of Metallic Source/Drain SOI MOSFETs Using Dopant Segregation at the Schottky Interface. IEEE Electron Device Letters, 2009, 30, 1197-1199.	2.2	25
63	Improved Characterization Methology for MOSFETs up to 220 GHz. IEEE Transactions on Microwave Theory and Techniques, 2009, 57, 1237-1243.	2.9	21
64	Effect of gate length in InAs/AlSb HEMTs biased for low power or high gain. Solid-State Electronics, 2008, 52, 775-781.	0.8	12
65	High-Frequency Noise Performance of 60-nm Gate-Length FinFETs. IEEE Transactions on Electron Devices, 2008, 55, 2718-2727.	1.6	104
66	RF Small-Signal Analysis of Schottky-Barrier p-MOSFET. IEEE Transactions on Electron Devices, 2008, 55, 1192-1202.	1.6	34
67	Nonlinear Characterization and Modeling of Carbon Nanotube Field-Effect Transistors. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 1505-1510.	2.9	6
68	Electrical Characterization and Small-Signal Modeling of InAs/AlSb HEMTs for Low-Noise and High-Frequency Applications. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 2685-2691.	2.9	37
69	Lateral Asymmetry in Silicon MOSFETs: A new path to improve their Microwave Noise Performance. , 2008, , .		0
70	Fabrication technology and device performances of ultra-short 30-nn-gate pseudomorphic In_{0.52}Al_{0.48}As/In_{0.75}Ga_{0.25}As HEMTs. , 2008, , .		2
71	High-Voltage HBTs Compatible with High-Speed SiGe BiCMOS Technology. , 2008, , .		0
72	Recent advances in metallic source/drain MOSFETs. , 2008, , .		6

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73	Industrial MHEMT Technologies for 80 - 220 GHz Applications. , 2008, , .		9
74	SiGe HBTs featuring f_T â‰«400GHz at room temperature. , 2008, , .		15
75	HF Characterisation of sub-100nm UTB-FDSOI with TiN/HfO2 Gate stack. , 2008, , .		3
76	In-situ silicon integrated tuner for automated on-wafer MMW noise parameters extraction of Si HBT and MOSFET in the range 60–110GHz. , 2008, , .		1
77	Selective wet chemical etching of GaInSb and AlInSb for 6.25 Ã... HBT fabrication. , 2008, , .		1
78	Small Signal and Noise Equivalent Circuit for CMOS 65 nm up to 110 GHz. , 2008, , .		12
79	Si/SiGe HBTs for Millimeter-wave BiCMOS Technologies. , 2008, , .		4
80	Characterization of Carbon Nanotube Field Effect Transistors using an active load pull LSNA setup. , 2008, , .		2
81	MOSFETs RF Noise Optimization via Channel Engineering. IEEE Electron Device Letters, 2008, 29, 118-121.	2.2	17
82	AlSb/InAs HEMTs on InP substrate using wet and dry etching for mesa isolation. , 2008, , .		3
83	Current gain enhancement in GaAsSb/InP - DHBT type grown by MBE with a graded composition AlInP emitter. , 2008, , .		1
84	Body-Biasing Control on Zero-Temperature-Coefficient in Partially Depleted SOI MOSFET. , 2008, , .		6
85	Low Temperature Implementation of Dopant-Segregated Band-edge Metallic S/D junctions in Thin-Body SOI p-MOSFETs. , 2007, , .		17
86	High Frequency Noise Performances of Silicon and III-V Field Effect Transistor. AIP Conference Proceedings, 2007, , .	0.3	2
87	Benchmarking of low band gap III-V based-HEMTs and sub-100nm CMOS under low drain voltage regime. , 2007, , .		0
88	65 nm HR SOI CMOS Technology: emergence of Millimeter-Wave SoC. Radio Frequency Integrated Circuits (RFIC) Symposium, IEEE, 2007, , .	0.0	9
89	Efficient De-Embedding Technique for 110-GHz Deep-Channel-MOSFET Characterization. IEEE Microwave and Wireless Components Letters, 2007, 17, 301-303.	2.0	13
90	High-Speed SiGe BiCMOS Technologies: 120-nm Status and End-of-Roadmap Challenges. , 2007, , .		31

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91	Characterization of insulated-gate versus schottky-gate InAs/AlSb HEMTs. , 2007, , .		1
92	Coupling on-wafer measurement errors and their impact on calibration and de-embedding up to 110 GHz for CMOS millimeter wave characterizations. , 2007, , .		14
93	Gigahertz frequency flexible carbon nanotube transistors. Applied Physics Letters, 2007, 91, 153111.	1.5	99
94	Investigation of High Frequency Performance for Schottky-Barrier p-MOSFET. , 2007, , .		4
95	40GHz Low Noise Receiver Circuits using BCB Above-Silicon Technology Optimized for Millimeter-wave Applications. , 2007, , .		1
96	DC and RF Performance of 0.2-0.4 /spl mu/m Gate Length InAs/AlSb HEMTs. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	1
97	1.8 dB insertion loss 200 GHz CPW band pass filter integrated in HR SOI CMOS Technology. , 2007, , .		28
98	Millimeter wave design with 65 nm LP SOI HR CMOS technology. , 2007, , .		2
99	80 GHz low noise amplifiers in 65nm CMOS SOI. , 2007, , .		18
100	(Cl2:Ar) ICP/RIE Dry Etching of Al(Ga)Sb FOR AlSb/InAs HEMTs. , 2007, , .		8
101	Intrinsic current gain cutoff frequency of 30GHz with carbon nanotube transistors. Applied Physics Letters, 2007, 90, 233108.	1.5	102
102	A 200-GHz True E-Mode Low-Noise MHEMT. IEEE Transactions on Electron Devices, 2007, 54, 1626-1632.	1.6	6
103	65 nm RFCMOS technologies with bulk and HR SOI substrate for millimeter wave passives and circuits characterized up to 220 GHZ. , 2006, , .		29
104	State of the art 200 GHz passive components and circuits integrated in advanced thin SOI CMOS technology on High Resistivity substrate. , 2006, , .		12
105	An 8-GHz f/sub t/ carbon nanotube field-effect transistor for gigahertz range applications. IEEE Electron Device Letters, 2006, 27, 681-683.	2.2	54
106	Noise and Dynamic Cryogenic performance of Metamorphic Transistors from 20 to 42 GHz. , 2006, , .		1
107	Directed assembly for carbon nanotube device fabrication. , 2006, , .		6
108	Linear, Noise and Nonlinear HF Models for Advanced CMOS Technology. , 2006, , .		1

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109	Active properties of carbon nanotube field-effect transistors deduced from S parameters measurements. IEEE Nanotechnology Magazine, 2006, 5, 335-342.	1.1	25
110	Analysis and modeling of substrate impedance network in RF CMOS. , 2006, , .		4
111	InP-Based InAlAs/InGaAs Double-Gate Transistors Beyond Conventional HEMT's Limitations. , 2006, , .		0
112	Dynamic response of carbon nanotube field-effect transistors analyzed by S-parameters measurement. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 135, 294-296.	1.7	5
113	A microscopic interpretation of the RF noise performance of fabricated FDSOI MOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 523-532.	1.6	17
114	High-Frequency and Noise Performances of 65-nm MOSFET at Liquid Nitrogen Temperature. IEEE Transactions on Electron Devices, 2006, 53, 1902-1908.	1.6	27
115	A Monte Carlo investigation of the RF performance of partially-depleted SOI MOSFETs. Semiconductor Science and Technology, 2006, 21, 273-278.	1.0	5
116	High frequency noise of SOI MOSFETs: performances and limitations (Invited Paper). , 2005, , .		9
117	Fabrication and characterization of low-loss TFMS on silicon substrate up to 220 GHz. IEEE Transactions on Microwave Theory and Techniques, 2005, 53, 301-305.	2.9	41
118	130-nm Partially Depleted SOI MOSFET Nonlinear Model Including the Kink Effect for Linearity Properties Investigation. IEEE Transactions on Electron Devices, 2005, 52, 2809-2812.	1.6	12
119	On the high-frequency noise figures of merit and microscopic channel noise sources in fabricated 90 nm PD SOI MOSFETs. AIP Conference Proceedings, 2005, , .	0.3	0
120	Investigation of longitudinal velocity fluctuations in MOSFETs by means of ensemble Monte Carlo simulation. AIP Conference Proceedings, 2005, , .	0.3	0
121	Noise in SOI MOSFETs and Gate-All Around Transistors. AIP Conference Proceedings, 2005, , .	0.3	2
122	Noise Performance at Cryogenic Temperature of Microwave SiGeC Low Noise Amplifier using BiCMOS Technology. AIP Conference Proceedings, 2005, , .	0.3	0
123	A metamorphic GaAs HEMT distributed amplifier with 50 GHz bandwidth and low noise for 40 Gbits/s. , 2005, , .		9
124	Design of narrow band-pass planar filters for millimeter-wave applications up to 220 GHz. , 2005, , .		10
125	Microwave and noise performance of SiGe BiCMOS HBT under cryogenic temperatures. IEEE Electron Device Letters, 2005, 26, 105-108.	2.2	20
126	A 40 GHz single-ended down-conversion mixer in 0.13 /spl mu/m SiGeC BiCMOS HBT. IEEE Microwave and Wireless Components Letters, 2005, 15, 496-498.	2.0	11

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127	Impact of Downscaling on High-Frequency Noise Performance of Bulk and SOI MOSFETs. IEEE Transactions on Electron Devices, 2004, 51, 1605-1612.	1.6	28
128	Noise modeling in fully depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 813-825.	0.8	33
129	High Microwave and Noise Performance of 0.17-<tex>$muhbox m$</tex>AlGaNâ€“GaN HEMTs on High-Resistivity Silicon Substrates. IEEE Electron Device Letters, 2004, 25, 167-169.	2.2	38
130	Thermal de-embedding procedure for cryogenic on-wafer high-frequency noise measurement. , 2004, , .		1
131	Noise modeling and performance in 0.15-Î¼m fully depleted SOI MOSFET. , 2004, , .		3
132	Wide- and narrow-band bandpass coplanar filters in the W -frequency band. IEEE Transactions on Microwave Theory and Techniques, 2003, 51, 784-791.	2.9	31
133	What are the limiting parameters of deep-submicron MOSFETs for high frequency applications?. IEEE Electron Device Letters, 2003, 24, 189-191.	2.2	107
134	A new empirical nonlinear model for sub-250 nm channel MOSFET. IEEE Microwave and Wireless Components Letters, 2003, 13, 449-451.	2.0	25
135	Impact of down scaling on high-frequency noise performance of bulk and SOI MOSFETs. , 2003, , .		2
136	High-frequency noise in FDSOI MOSFETs: a Monte Carlo investigation. , 2003, , .		2
137	Numerical and experimental study of a 0.25 Âµm fully-depleted silicon-on-insulator MOSFET: static and dynamic radio-frequency behaviour. Semiconductor Science and Technology, 2002, 17, 1149-1156.	1.0	9
138	Fast electromagnetic characterisation method of thin planar materials using coplanar line up to V-band. Electronics Letters, 2002, 38, 373.	0.5	6
139	Very high broadband electromagnetic characterization method of film-shaped materials using coplanar. Microwave and Optical Technology Letters, 2002, 33, 352-355.	0.9	9
140	0.25 Î¼m fully depleted SOI MOSFETs for RF mixed analog-digital circuits, including a comparison with partially depleted devices with relation to high frequency noise parameters. Solid-State Electronics, 2002, 46, 379-386.	0.8	20
141	Transmission Lines on Low Resistivity Silicon Substrate for MMICs Applications. , 2001, , .		7
142	Temperature noise model for FET mixers. AIP Conference Proceedings, 2000, , .	0.3	1
143	Title is missing!. Analog Integrated Circuits and Signal Processing, 2000, 25, 133-155.	0.9	6
144	Ridged waveguide to microstrip transition for electromagnetic characterisation of materials in V-band. Electronics Letters, 2000, 36, 1468.	0.5	16

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145	Noise analysis in devices under nonlinear operation. Solid-State Electronics, 1999, 43, 21-26.	0.8	22
146	High-frequency four noise parameters of silicon-on-insulator-based technology MOSFET for the design of low-noise RF integrated circuits. IEEE Transactions on Electron Devices, 1999, 46, 1733-1741.	1.6	61
147	<title>94-GHz MMIC CPW low-noise amplifier on InP</title>. , 1999, , .		0
148	Noise modeling in MESFET and HEMT mixers using a uniform noisy line model. IEEE Transactions on Electron Devices, 1998, 45, 2207-2212.	1.6	17
149	A new extrinsic equivalent circuit of HEMT's including noise for millimeter-wave circuit design. IEEE Transactions on Microwave Theory and Techniques, 1998, 46, 1231-1236.	2.9	21
150	Silicon-On-Insulator-Based Technology MOSFET : Prospects For Application to Low Noise RF Integrated Circuits. , 1998, , .		0
151	A New Nonlinear Noise Model for MESFET and HEMT Mixers Suitable for CAD Software. , 1998, , .		1
152	Direct Extraction of the Nonquasi-Static Small-Signal Model of MOSFET's. , 1998, , .		0
153	Modeling of Passive Coplanar Elements for W-band ICS, Experimental Verification Up to 110 GHz and Parasitic Mode Coupling Study. , 1998, , .		2
154	Direct extraction of the series equivalent circuit parameters for the small-signal model of SOI MOSFETs. , 1997, 7, 408-410.		50
155	On the validity of a new extrinsic equivalent circuit including noise of HEMTs required for millimeter wave circuit design. Annales Des Telecommunications/Annals of Telecommunications, 1997, 52, 140-144.	1.6	0
156	HEMTs extrinsic noise model for millimeter waves integrated circuits design. , 1996, , .		3
157	Influence of the gate leakage current on the noise performance of MESFETs and MODFETs. Solid-State Electronics, 1995, 38, 1081-1087.	0.8	43
158	Microscopic noise modeling and macroscopic noise models: how good a connection? [FETs]. IEEE Transactions on Electron Devices, 1994, 41, 779-786.	1.6	50
159	Helena: A friendly software for calculating the DC, AC, and noise performance of HEMTs. The International Executive, 1993, 3, 14-28.	0.2	16
160	A new method for on wafer noise measurement. IEEE Transactions on Microwave Theory and Techniques, 1993, 41, 375-381.	2.9	106
161	High-frequency performance of submicrometer channel-length silicon MOSFETs. IEEE Electron Device Letters, 1991, 12, 667-669.	2.2	40
162	A new method for determining the FET small-signal equivalent circuit. IEEE Transactions on Microwave Theory and Techniques, 1988, 36, 1151-1159.	2.9	1,279

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163	DÃ©termination rapide et prÃ©cise du schÃ©ma Ã©quivalent â€œpetit signalâ€•des transistors Ã effet de champ. Annales Des Telecommunications/Annals of Telecommunications, 1988, 43, 274-281.	1.6	0
164	Integration of ultra wide band high pass filter using high performance inductors in advanced high resistivity SOI CMOS technology. , 0, , .		2
165	Influence of gate offset spacer width on SOI MOSFETs HF properties. , 0, , .		2
166	A compact low noise amplifier in SiGe:C BiCMOS technology for 40 GHz wireless communications. , 0, , .		5
167	State of the art integrated millimeter wave passive components and circuits in advanced thin SOI CMOS technology on High Resistivity substrate. , 0, , .		16